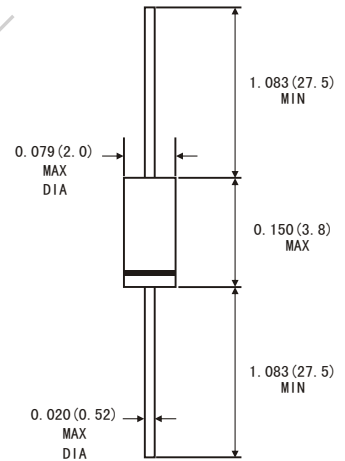


FEATURES

- Metal-on-silicon junction
 - Low turn-on voltage
 - Ultrafast switching speed
 - Primarily intended for high level UHF mixers and ultrafast switching applications
- The diode is also available in the MiniMELF case with type designation LL19.
- High temperature soldering guaranteed: 260°C / 10 seconds at terminals
 - Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



DO-35



MECHANICAL DATA

- Case: DO-35 glass case
- Polarity: color band denotes cathode end
- Weight: Approx. 0.13 gram

ABSOLUTE RATINGS(LIMITING VALUES)

| | Symbols | Value | Units |
|--|-----------|-------------|-------|
| Peak Reverse Voltage | V_{RRM} | 10 | V |
| Forward Continuous Current | I_F | 30 | mA |
| Surge non repetitive forward current $t_p \leq 1s$ | I_{FSM} | 60 | mA |
| Junction and Storage temperature range | T_{STG} | -65 to +150 | °C |
| | T_J | -65 to +150 | °C |
| Maximum Lead Temperature for Soldering during 10s at 4mm from Case | T_L | 230 | °C |

ELECTRICAL CHARACTERISTICS

| | Symbols | Min. | Typ. | Max. | Unis |
|--|-----------------|------|------|------|------|
| Reverse breakover voltage at $I_R=10\mu A$ | V_R | 10 | | | V |
| | | | | | V |
| Leakage current at $V_R=5V$ | I_R | | | 100 | nA |
| Forward voltage drop at $I_F=1mA$ Test pulse: $t_p \leq 300\mu s$ $\delta < 2\%$ $I_F=35mA$ | V_F | | | 0.40 | V |
| | | | | 1.0 | V |
| Junction Capacitance at $V_R=0V$, $f=1GHz$ | C_J | | | 1.2 | pF |
| Thermal resistance | $R_{\theta JA}$ | | | 400 | K/W |

RATINGS AND CHARACTERISTICS CURVES BAT19

Figure 1. Forward current versus forward voltage at low level (typical values)

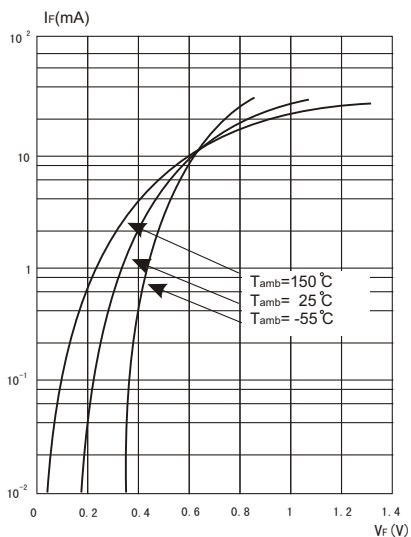


Figure 2. Capacitance C versus reverse applied voltage V_R (typical values)

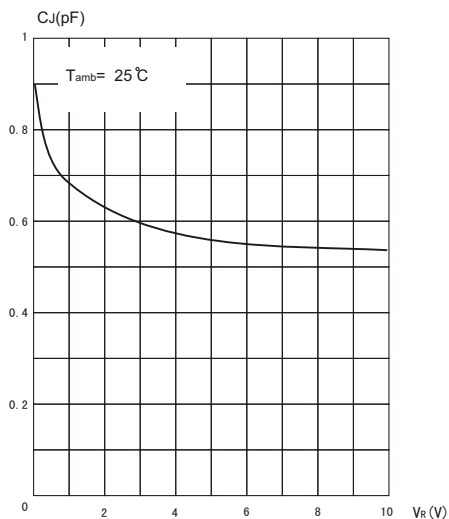


Figure 3. Reverse current versus ambient temperatures

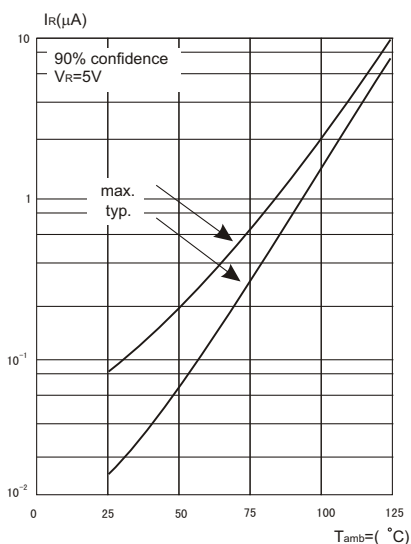


Figure 4. Reverse current versus continuous Reverse voltage (typical values)

